

微纳光电子材料与器件工艺原理

Emerging Technologies

Xing Sheng 盛兴

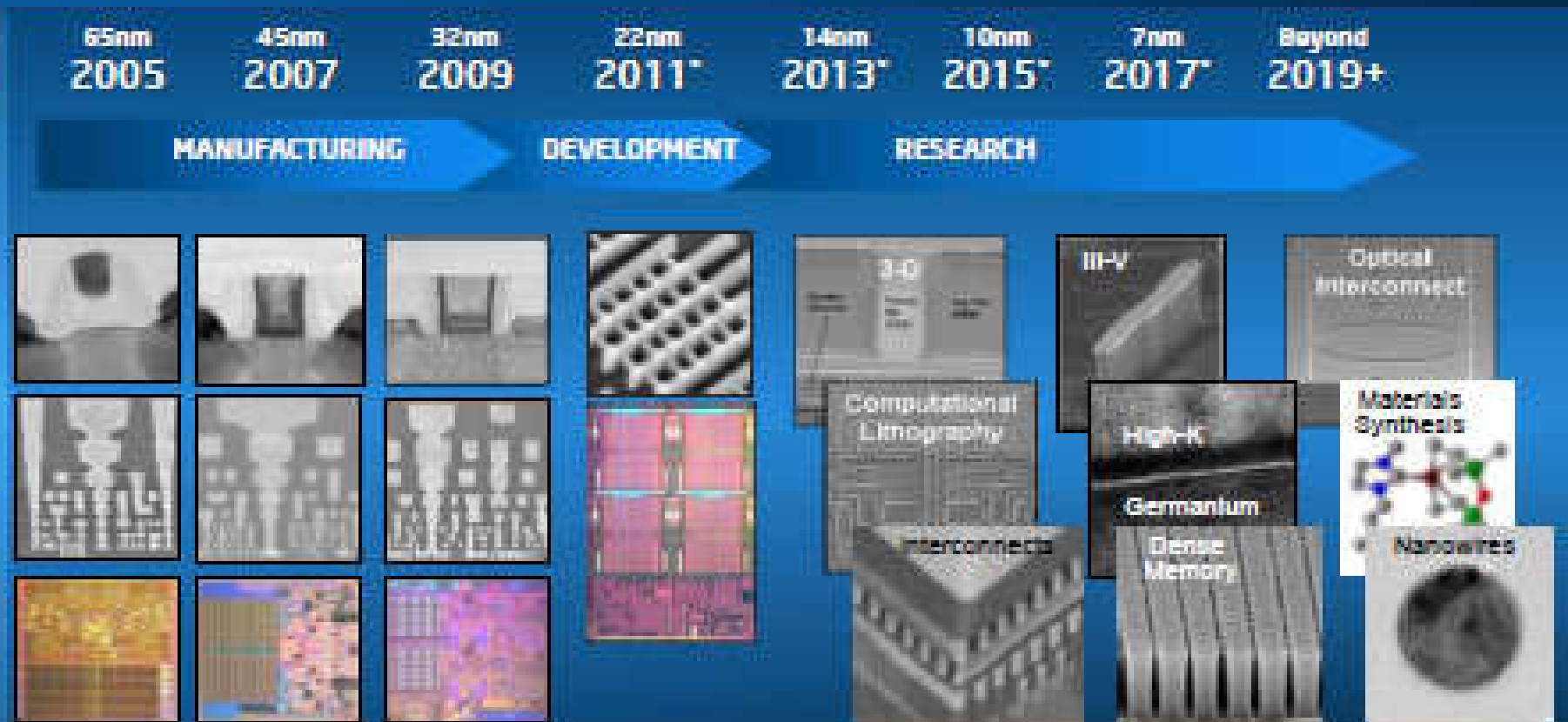
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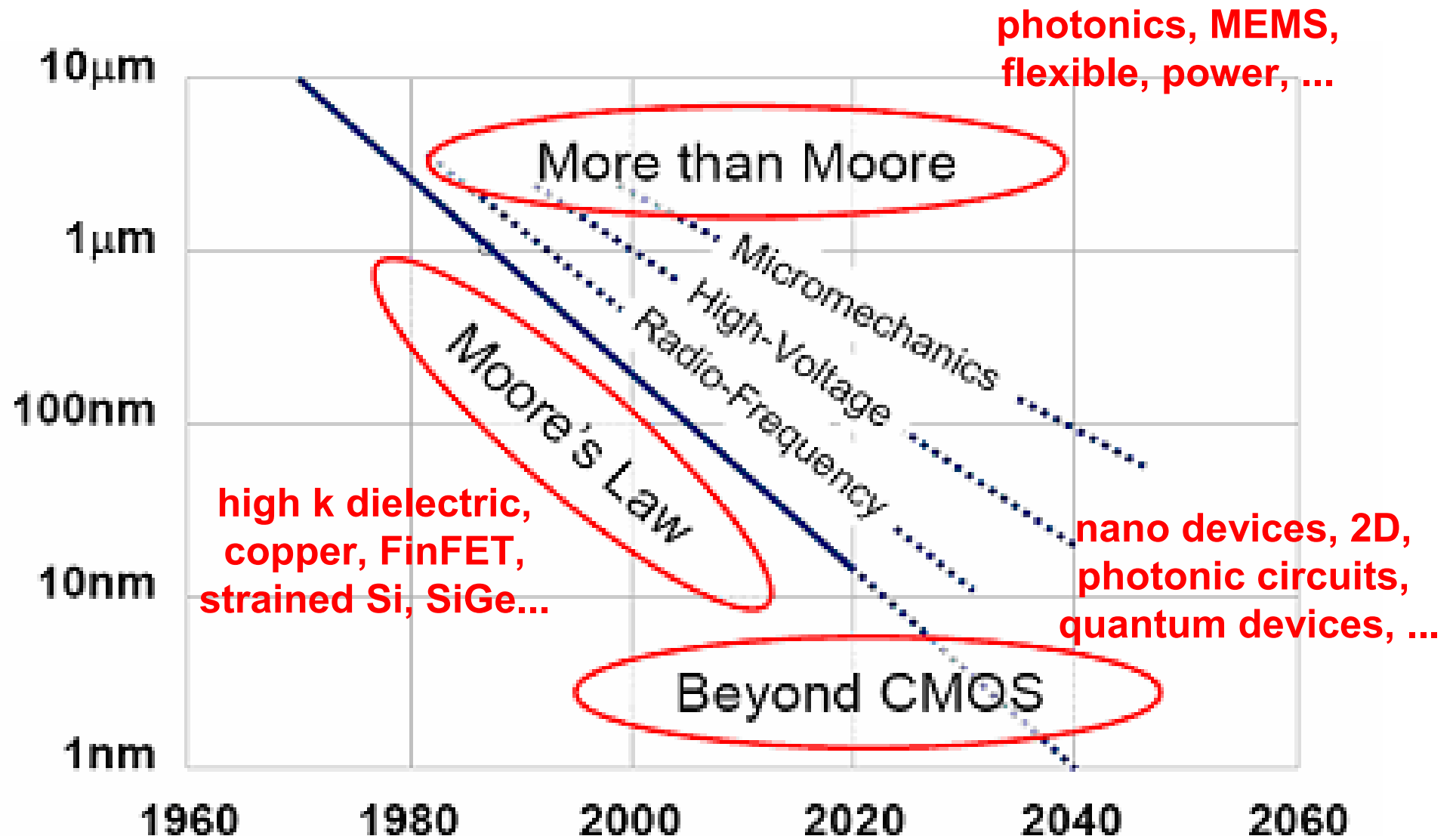


New Opportunities

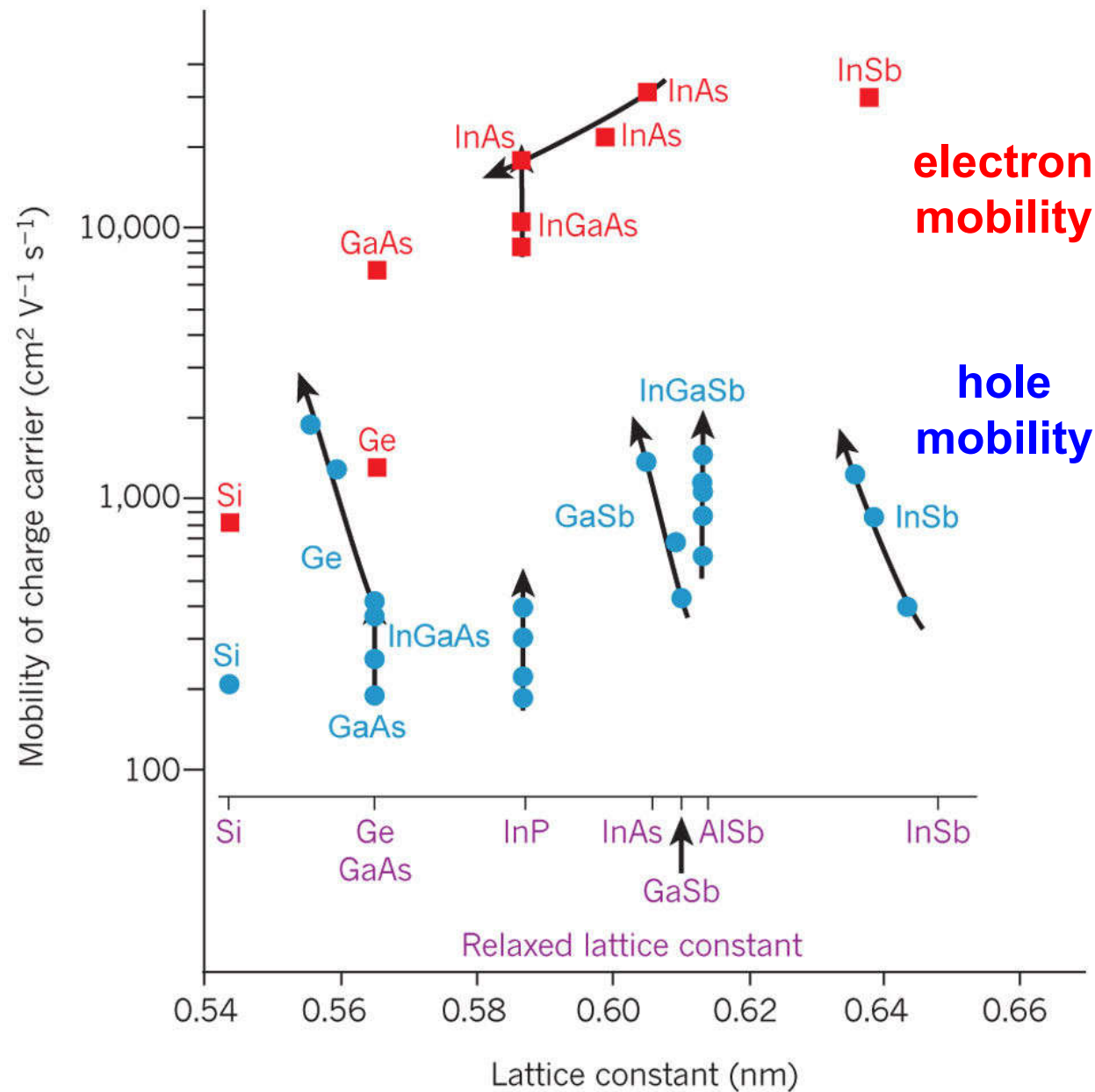
We Expect Technology Innovation to Continue



New Opportunities



High Electron Mobility Transistor (HEMT)

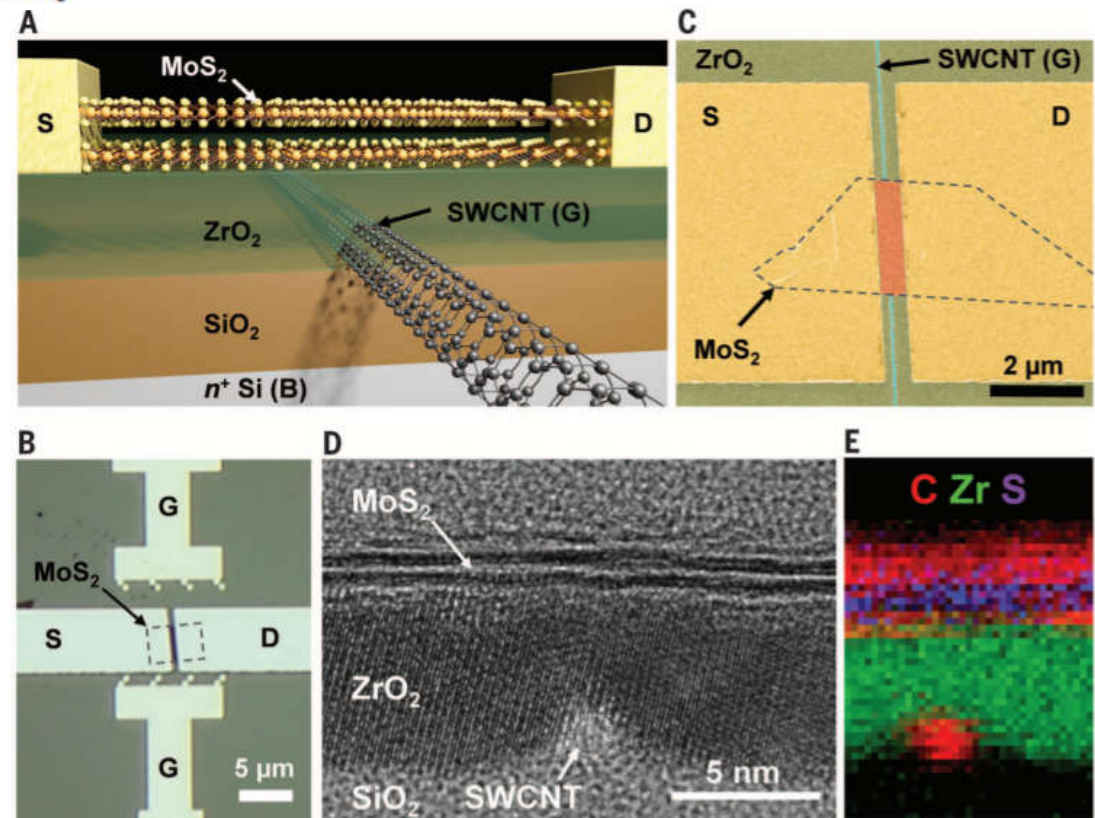


Nano-Transistors

DEVICE TECHNOLOGY

MoS₂ transistors with 1-nanometer gate lengths

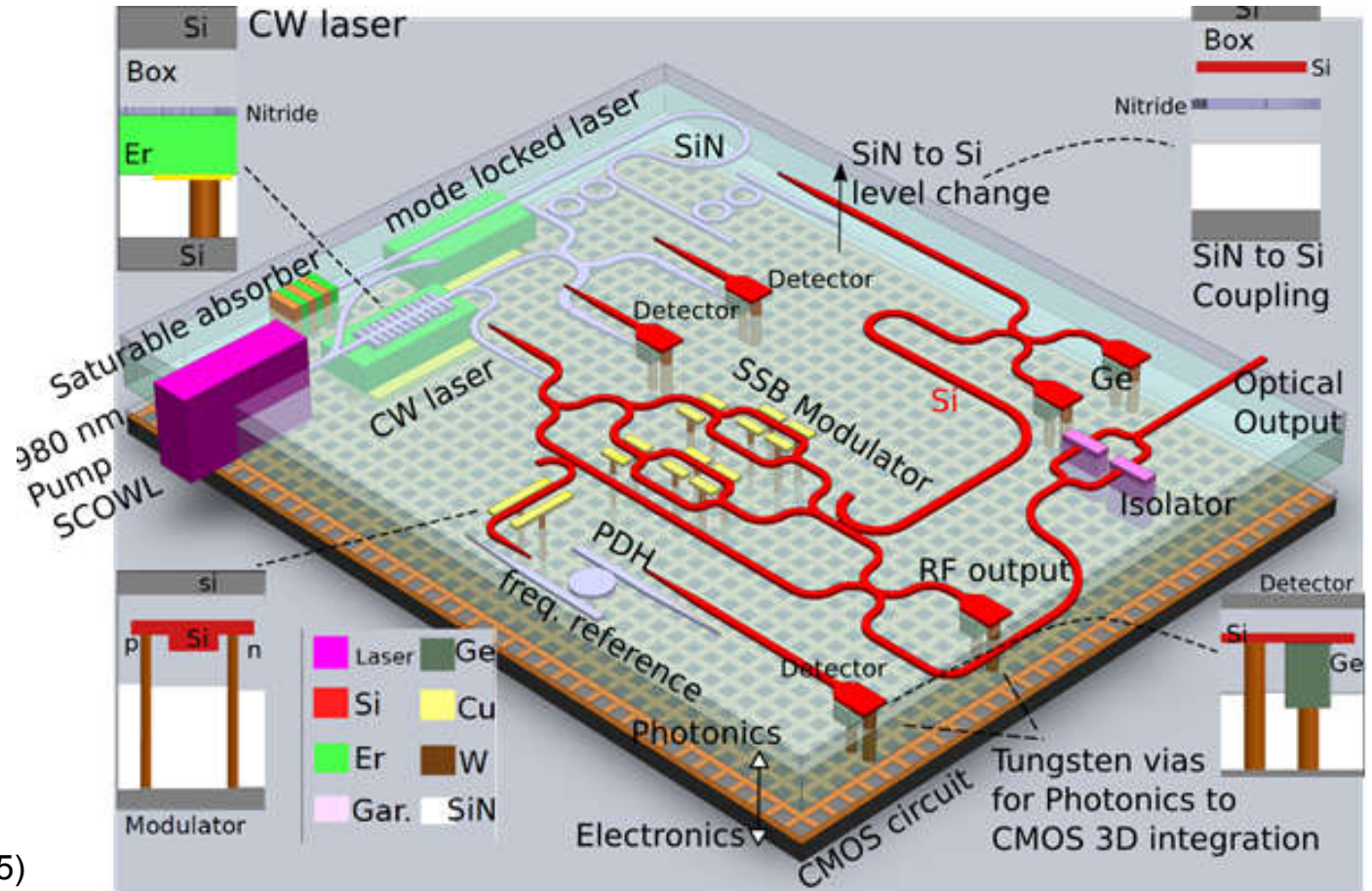
Sujay B. Desai,^{1,2,3} Surabhi R. Madhvapathy,^{1,2} Angada B. Sachid,^{1,2}
 Juan Pablo Llinas,^{1,2} Qingxiao Wang,⁴ Geun Ho Ahn,^{1,2} Gregory Pitner,⁵ Moon J. Kim,⁴
 Jeffrey Bokor,^{1,2} Chenming Hu,¹ H.-S. Philip Wong,⁵ Ali Javey^{1,2,3*}



Photonic Integrated Circuits

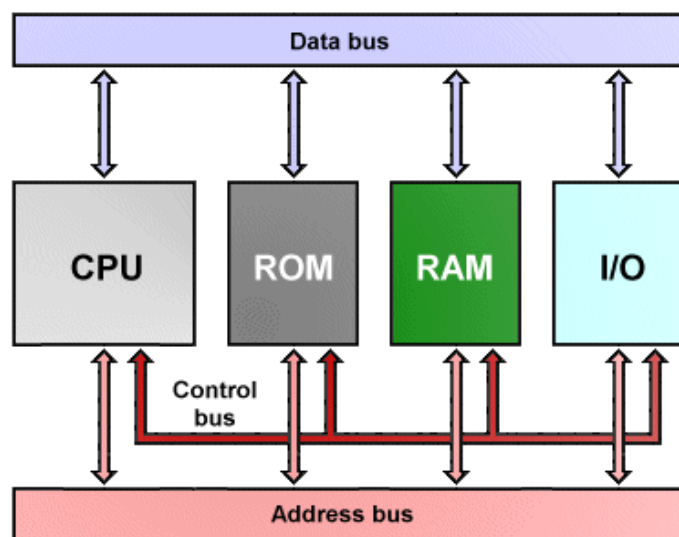
Single-chip microprocessor that communicates directly using light

Chen Sun^{1,2*}, Mark T. Wade^{3*}, Yunsup Lee^{1*}, Jason S. Orcutt^{2†*}, Luca Alloatti², Michael S. Georgas², Andrew S. Waterman¹, Jeffrey M. Shainline^{3†}, Rimantas R. Avizienis¹, Sen Lin¹, Benjamin R. Moss², Rajesh Kumar³, Fabio Pavanello³, Amir H. Atabaki², Henry M. Cook¹, Albert J. Ou¹, Jonathan C. Leu², Yu-Hsin Chen², Krste Asanović¹, Rajeev J. Ram², Miloš A. Popović³ & Vladimir M. Stojanović¹

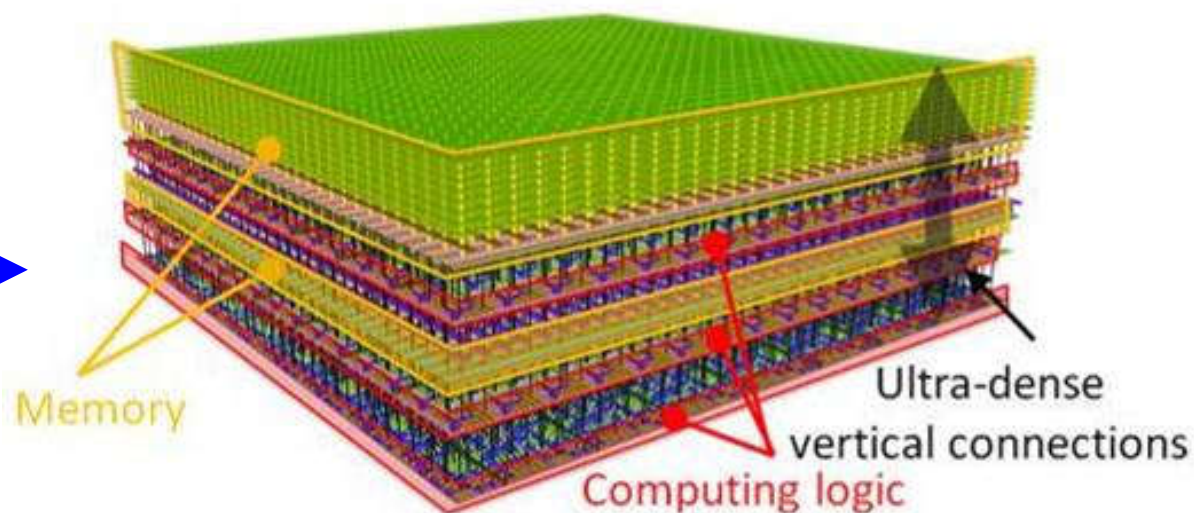


3D IC

- Logic + Memory + Sensing + ...

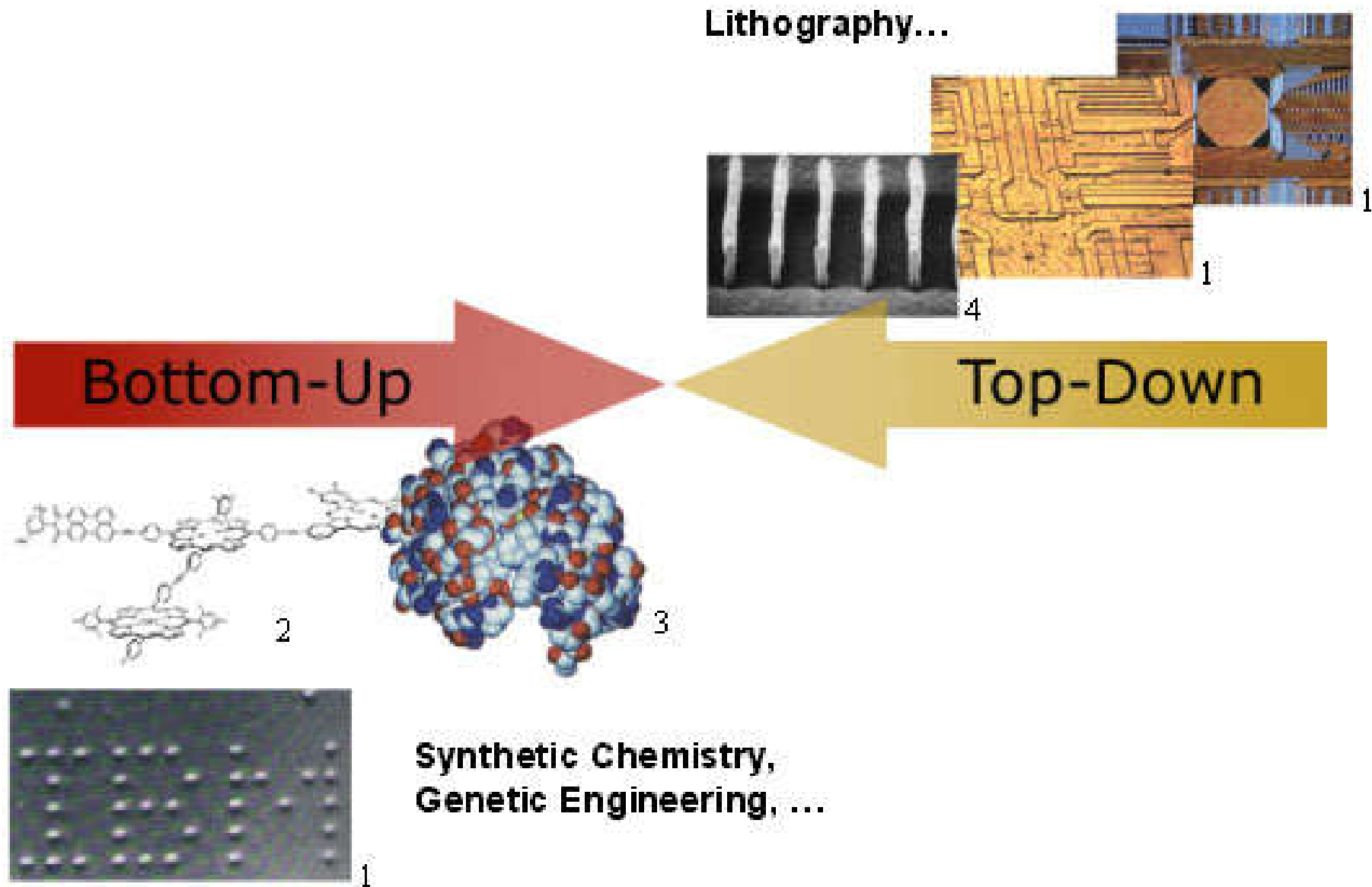


conventional



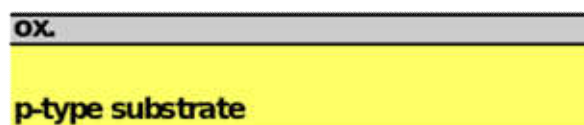
3D IC

Top Down vs. Bottom Up

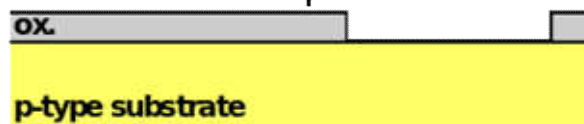


Top Down Approaches

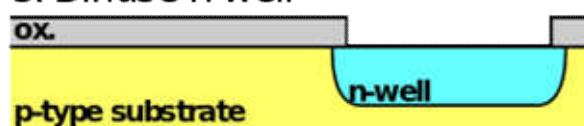
1. Grow field oxide



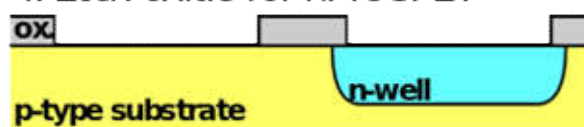
2. Etch oxide for pMOSFET



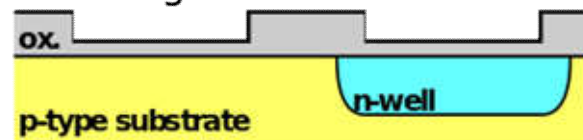
3. Diffuse n-well



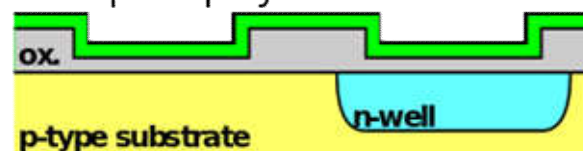
4. Etch oxide for nMOSFET



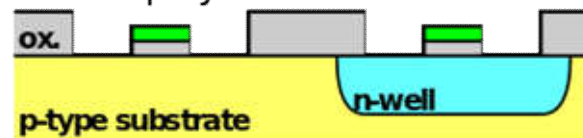
5. Grow gate oxide



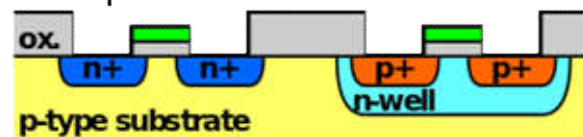
6. Deposit polysilicon



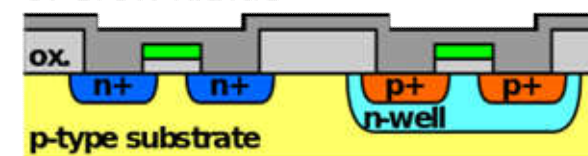
7. Etch polysilicon and oxide



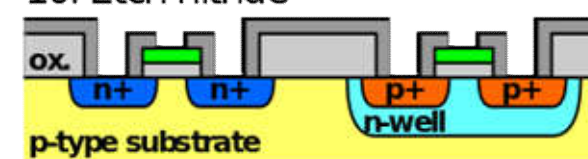
8. Implant sources and drains



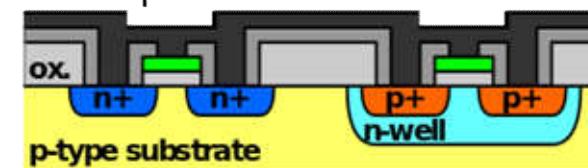
9. Grow nitride



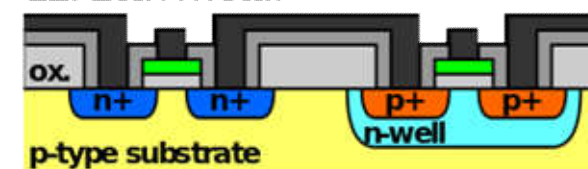
10. Etch nitride



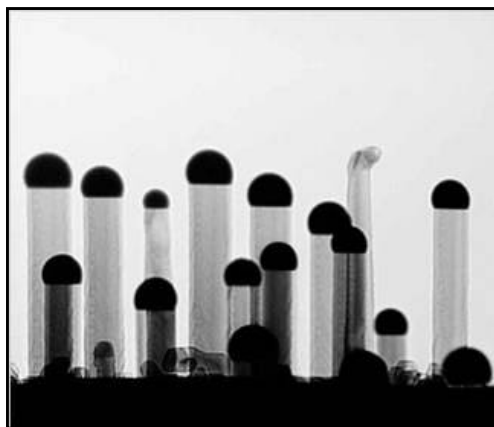
11. Deposit metal



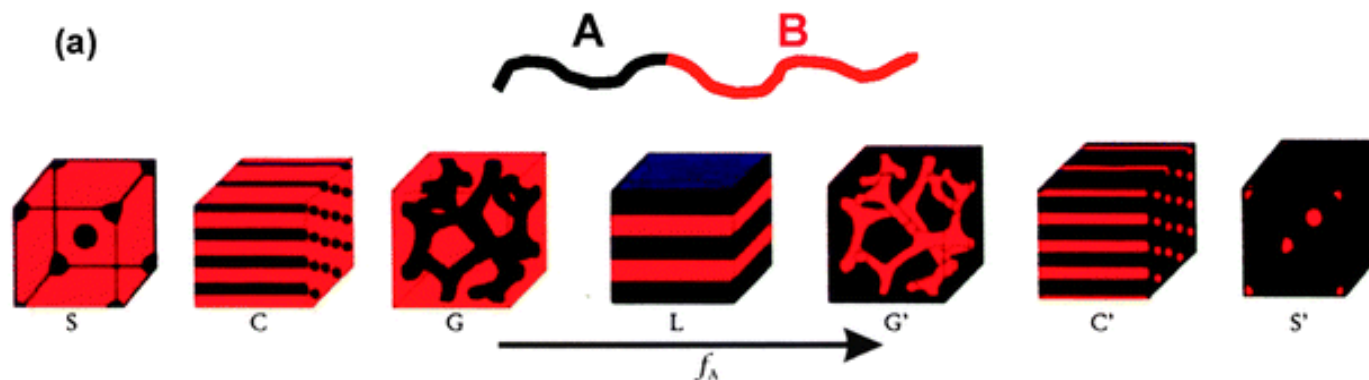
12. Etch metal



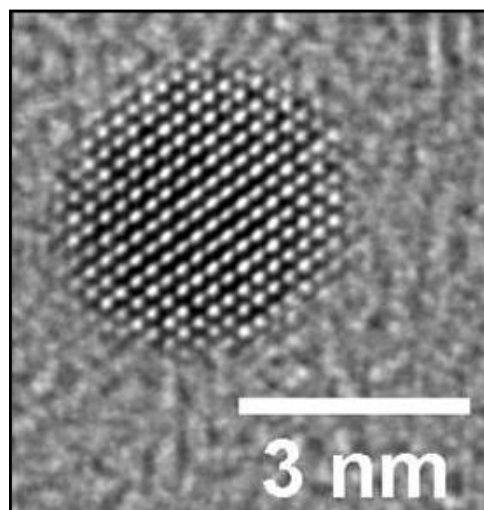
Bottom Up Approaches



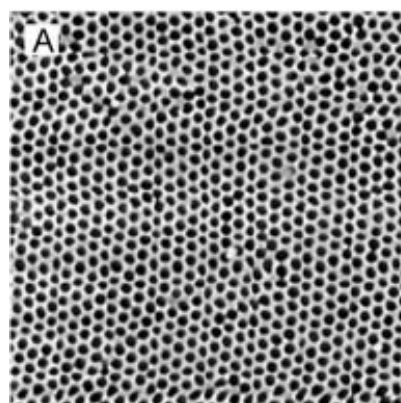
nanowire growth



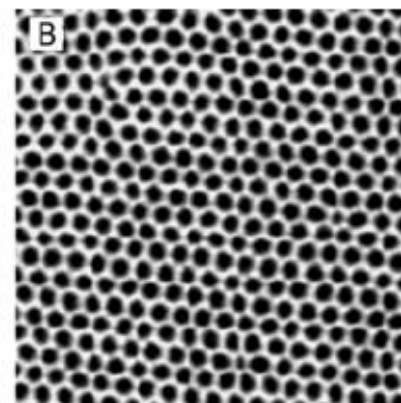
block copolymer assembly



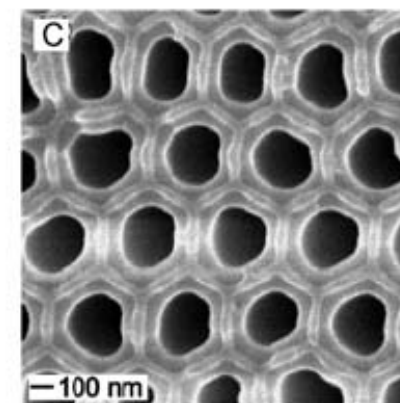
quantum dot



0.3 M H_2SO_4 , 25 V
 $D_p = 60$ nm



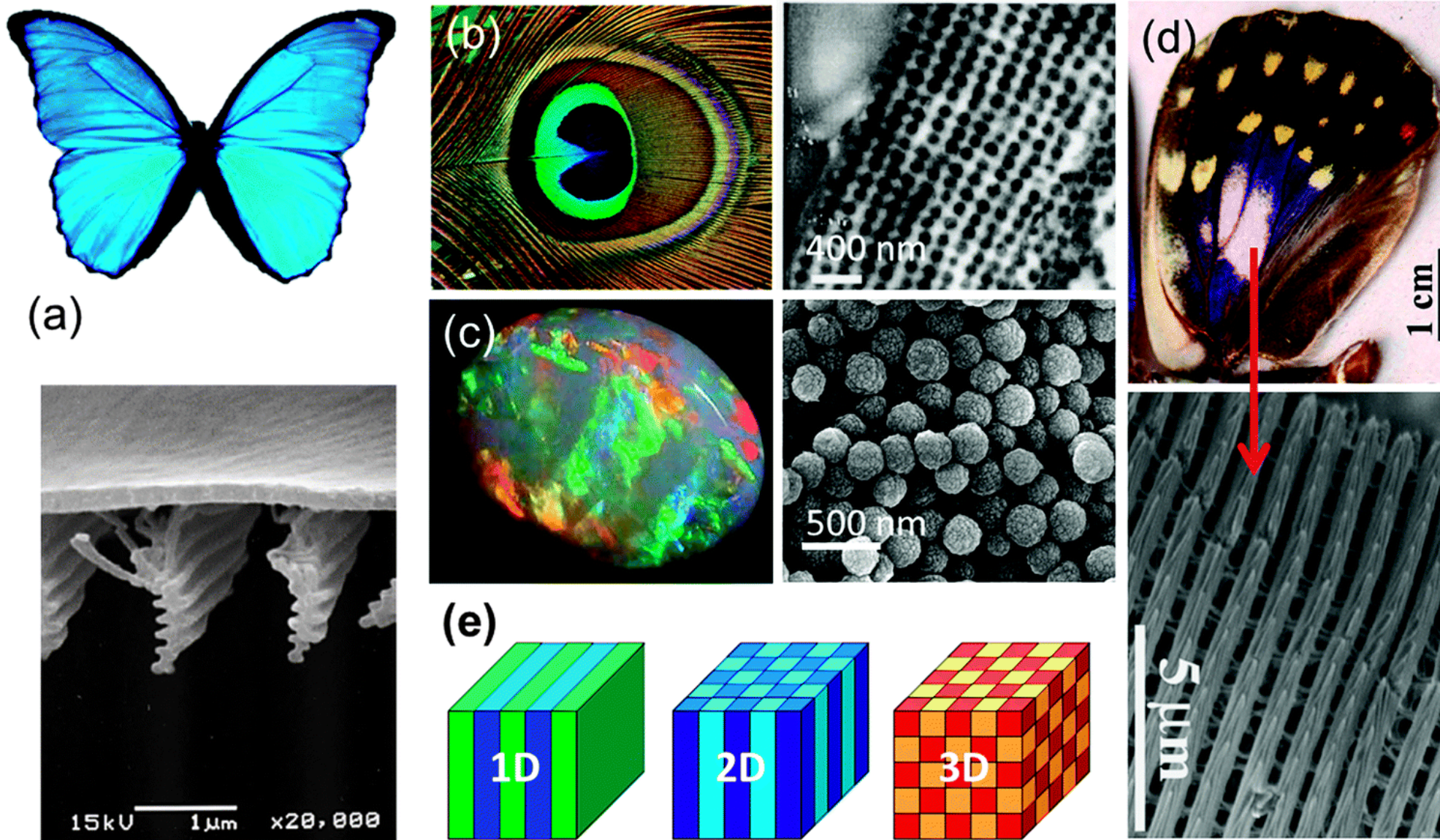
0.5 $\text{C}_2\text{H}_2\text{O}_4$, 40 V
 $D_p = 100$ nm



1.1 M H_3PO_4 , 160 V
 $D_p = 420$ nm

anodized alumina

Nano Structures in Nature



Summary

"There is plenty of room at the bottom."

— Richard Feynman

***"Scientists discover the world that exists;
Engineers create the world that never was."***

— Theodore van Karman

Thank you for your attention